Amendments to the Claims

Claims 1-14 (Cancelled).

15. (Currently amended) A plasma etching process comprising:

forming a masking layer over a substrate;

patterning the masking layer to form openings therein;

first etching material beneath the masking layer through the openings, the first etching extending the openings to outwardly expose a conductive silicon-comprising material at a base of the openings;

after the first etching, removing the masking layer from the substrate; and

after the removing and before subsequently depositing any material over the substrate, utilizing an oxygen-comprising plasma to entirely remove a residue from the outwardly exposed conductive silicon-comprising material, the plasma being generated from a gas having active components consisting of one or more members of the group consisting of O_2, O_3, H_2 and NH_3, the utilizing the oxygen-comprising plasma being subsequent to and independent of removing the masking layer.

16. (Previously presented) The plasma etching process of claim 15 wherein the plasma comprises O_3.

17. (Original) The plasma etching process of claim 15 wherein the plasma comprises hydrogen.

18. (Original) The plasma etching process of claim 17 wherein the hydrogen containing plasma is derived at least in part from H_2.

19. (Original) The plasma etching process of claim 17 wherein the hydrogen containing plasma is derived at least in part from NH_3.

20. (Original) The plasma etching process of claim 15 wherein the plasma is predominately comprised of hydrogen.

21. (Original) The plasma etching process of claim 15 wherein the temperature is at least 600°C.

22. (Previously presented) The plasma etching process of claim 15 wherein the residue is formed at least partially over the substrate during the first etching.

Claims 23-34 (Cancelled).

35. (Currently amended) A plasma etching process comprising:

forming a photoresist layer over a semiconductor substrate;

patterning the photoresist layer to form openings therethrough;

dry etching a BPSG layer immediately beneath the photoresist layer through the openings, the dry etching extending the openings to expose a monocrystalline silicon substrate material at a base surface of the openings and forming a carbon containing

polymer residue at least partially over the monocrystalline silicon substrate material at the base of the openings during the dry etching;

after the dry etching, removing the photoresist layer from the substrate; and

after the removing and before subsequently depositing any material over the substrate, plasma etching to entirely remove the carbon containing polymer residue from the monocrystalline silicon substrate material substantially selectively relative to the BPSG layer and relative to the monocrystalline silicon substrate material, the plasma etching being independent of the removing of the photoresist layer and utilizing a plasma generated from a gas having active components consisting of one or more members of the group consisting of O_2, O_3, H_2 and NH_3.

36. (Original) The plasma etching process of claim 35 wherein the plasma etching is conducted at a temperature of at least 400°C.

37. (Original) The plasma etching process of claim 35 wherein the plasma etching is conducted at a temperature of at least 600°C.

38. (Original) The plasma etching process of claim 35 wherein the plasma comprises oxygen.

39. (Original) The plasma etching process of claim 35 wherein the plasma comprises hydrogen.

40. (Original) The plasma etching process of claim 39 wherein the plasma is derived at least in part from H_2.

41. (Original) The plasma etching process of claim 39 wherein the plasma is derived at least in part from NH_3.

Claims 42-60 (Cancelled).